

μ A148 • μ A248 • μ A348 Quad Operational Amplifiers

Linear Division Operational Amplifiers

Description

The μ A148 series is a true quad μ A741. It consists of four independent, high gain, internally frequency compensated, low power operational amplifiers which have been designed to provide functional characteristics identical to those of the familiar μ A741 operational amplifier. In addition, the total supply current for all four amplifiers is comparable to the supply current of a single μ A741 type operational amplifier.

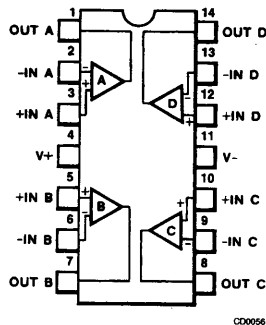
Other features include input offset currents and input bias currents which are much less than those of a standard μ A741. Also, excellent isolation between amplifiers has been achieved by independently biasing each amplifier and using layout techniques which minimize thermal coupling.

- μ A741 Op Amp Operating Characteristics
- Low Supply Current Drain
- Class AB Output Stage—No Crossover Distortion
- Lead Compatible With The μ A324 & μ A3403
- Low Input Offset Voltage—1.0 mV Typically
- Low Input Offset Current—4.0 nA Typically
- Low Input Bias Current—30 nA Typically
- Gain Bandwidth Product For μ A148 (Unity Gain)—1.0 MHz Typically
- High Degree Of Isolation Between Amplifiers—120 dB Typically
- Overload Protection For Inputs And Outputs

Absolute Maximum Ratings

Storage Temperature Range	
Ceramic DIP	-65°C to +175°C
Molded DIP	-65°C to +150°C
Operating Temperature Range	
Extended (μ A148M)	-55°C to +125°C
Industrial (μ A248V)	-25°C to +85°C
Commercial (μ A348C)	0°C to +70°C
Lead Temperature	
Ceramic DIP (soldering, 60 s)	300°C
Molded DIP (soldering, 10 s)	265°C
Internal Power Dissipation ^{1,2}	
14L-Molded DIP	1.04 W
14L-Ceramic DIP	1.36 W
Supply Voltage	
μ A148	± 22 V
μ A248, μ A348	± 18 V
Differential Input Voltage	
μ A148	± 44 V
μ A248, μ A348	± 36 V
Input Voltage	
μ A148	± 22 V
μ A248, μ A348	± 18 V
Output Short Circuit Duration ³	
	Indefinite

Connection Diagram 14-Lead DIP (Top View)



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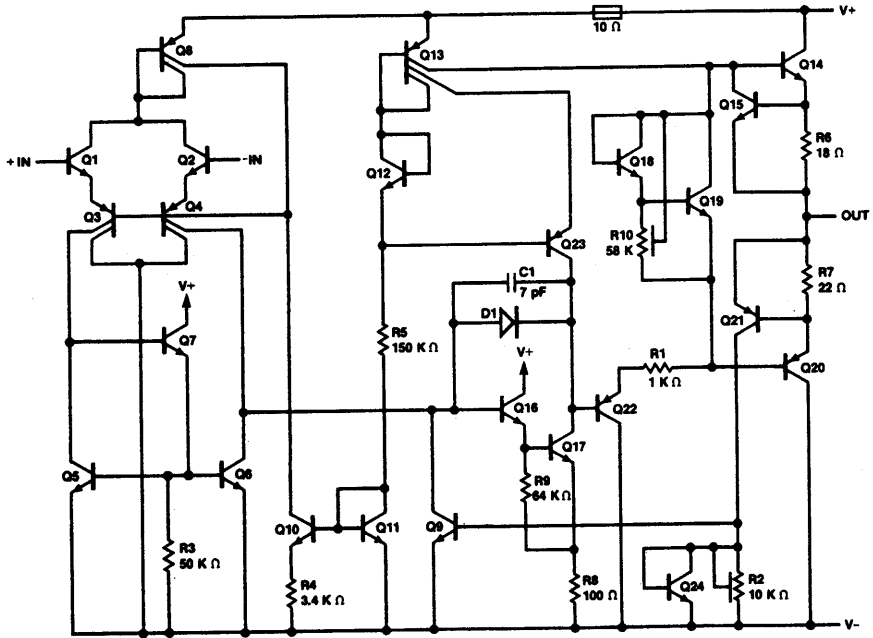
Order Information

Device Code	Package Code	Package Description
μ A148DM	6A	Ceramic DIP
μ A248DV	6A	Ceramic DIP
μ A248PV	9A	Molded DIP
μ A348DC	6A	Ceramic DIP
μ A348PC	9A	Molded DIP

Notes

1. T_J Max = 150°C for the Molded DIP, and 175°C for the Ceramic DIP.
2. Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 14-Lead Molded DIP at 8.3 mW/°C, and the 14-Lead Ceramic DIP at 9.1 mW/°C.
3. Any of the amplifier outputs can be shorted to ground indefinitely; however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

Equivalent Circuit (1/4 of Circuit)



 = CROSSUNDER

EQ00001F

μA148

Electrical Characteristics $T_A = 25^\circ\text{C}$, $V_{CC} = \pm 15\text{ V}$, unless otherwise specified.

DC Characteristics

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage	$R_S \leq 10\text{ k}\Omega$		1.0	5.0	mV
I_{IO}	Input Offset Current			4	25	nA
I_{IB}	Input Bias Current			30	100	nA
Z_i	Input Impedance		0.8	2.5		MΩ
I_{CC}	Supply Current (Total)			2.4	3.6	mA
I_{OS}	Output Short Circuit Current			25		mA
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10\text{ V}$, $R_L \geq 2.0\text{ k}\Omega$	50	160		V/mV
CS	Channel Separation	1.0 Hz $\leq f \leq 20\text{ kHz}$ (Input Referred)		-120		dB

The following specifications apply over the range of $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$.

V_{IO}	Input Offset Voltage	$R_S \leq 10\text{ k}\Omega$			6.0	mV
I_{IO}	Input Offset Current				75	nA
I_{IB}	Input Bias Current				325	nA
CMR	Common Mode Rejection	$R_S \leq 10\text{ k}\Omega$	70	90		dB
V_{IR}	Input Voltage Range		± 12			V
PSRR	Power Supply Rejection Ratio	$R_S \leq 10\text{ k}\Omega$	77	96		dB
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10\text{ V}$, $R_L \geq 2.0\text{ k}\Omega$	25			V/mV
V_{OP}	Output Voltage Swing	$R_L = 10\text{ k}\Omega$	± 12	± 13		V
		$R_L = 2.0\text{ k}\Omega$	± 10	± 12		

AC Characteristics

BW	Bandwidth			1.0		MHz
ϕ	Phase Margin	$A_V = 1.0$		60		degrees
SR	Slew Rate	$A_V = 1.0$		0.5		V/μs

μA248

Electrical Characteristics $T_A = 25^\circ\text{C}$, $V_{CC} = \pm 15\text{ V}$, unless otherwise specified.

DC Characteristics

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage	$R_S \leq 10\text{ k}\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			4	50	nA
I_{IB}	Input Bias Current			30	200	nA
Z_I	Input Impedance		0.8	2.5		M Ω
I_{CC}	Supply Current (Total)			2.4	4.5	mA
I_{OS}	Output Short Circuit Current			25		mA
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10\text{ V}$, $R_L \geq 2.0\text{ k}\Omega$	25	160		V/mV
CS	Channel Separation	1.0 Hz $\leq f \leq 20\text{ kHz}$ (Input Referred)		-120		dB

The following specifications apply over the range of $-25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$.

V_{IO}	Input Offset Voltage	$R_S \leq 10\text{ k}\Omega$			7.5	mV
I_{IO}	Input Offset Current				125	nA
I_{IB}	Input Bias Current				500	nA
CMR	Common Mode Rejection	$R_S \leq 10\text{ k}\Omega$	70	90		dB
V_{IR}	Input Voltage Range		± 12			V
PSRR	Power Supply Rejection Ratio	$R_S \leq 10\text{ k}\Omega$	77	96		dB
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10\text{ V}$, $R_L \geq 2.0\text{ k}\Omega$	15			V/mV
V_{OP}	Output Voltage Swing	$R_L = 10\text{ k}\Omega$	± 12	± 13		V
		$R_L = 2.0\text{ k}\Omega$	± 10	± 12		

AC Characteristics

BW	Bandwidth			1.0		MHz
ϕ	Phase Margin	$A_V = 1.0$		60		degrees
SR	Slew Rate	$A_V = 1.0$		0.5		V/ μs

$\mu\text{A}348$

Electrical Characteristics $T_A = 25^\circ\text{C}$, $V_{CC} = \pm 15 \text{ V}$, unless otherwise specified.

DC Characteristics

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			4	50	nA
I_{IB}	Input Bias Current			30	200	nA
Z_I	Input Impedance		0.8	2.5		$\text{M}\Omega$
I_{CC}	Supply Current (Total)			2.4	4.5	mA
I_{OS}	Output Short Circuit Current			25		mA
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10 \text{ V}$, $R_L \geq 2.0 \text{ k}\Omega$	25	160		V/mV
CS	Channel Separation	$1.0 \text{ Hz} \leq f \leq 20 \text{ kHz}$ (Input Referred)		-120		dB

The following specifications apply over the range of $0^\circ\text{C} \leq T_A \leq +70^\circ\text{C}$.

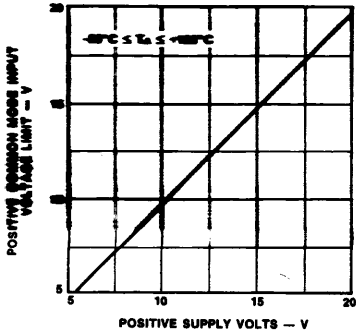
V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			7.5	mV
I_{IO}	Input Offset Current				100	nA
I_{IB}	Input Bias Current				400	nA
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$	70	90		dB
V_{IR}	Input Voltage Range		± 12			V
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	77	96		dB
A_{VS}	Large Signal Voltage Gain	$V_O = \pm 10 \text{ V}$, $R_L \geq 2.0 \text{ k}\Omega$	15			V/mV
V_{OP}	Output Voltage Swing	$R_L = 10 \text{ k}\Omega$	± 12	± 13		V
		$R_L = 2.0 \text{ k}\Omega$	± 10	± 12		

AC Characteristics

BW	Bandwidth			1.0		MHz
ϕ	Phase Margin	$A_V = 1.0$		60		degrees
SR	Slew Rate	$A_V = 1.0$		0.5		V/ μs

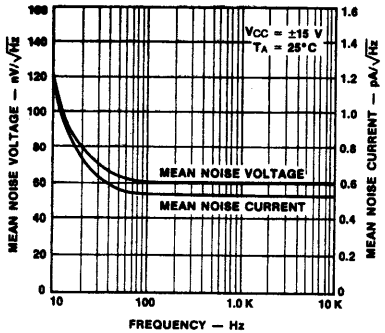
Typical Performance Curves

Positive Common Mode Input Voltage Limit vs Supply Voltage



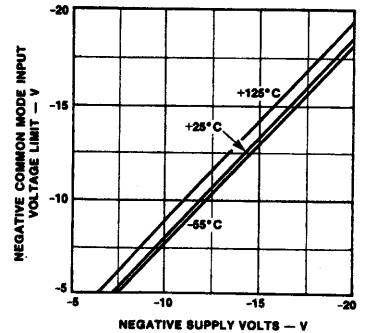
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Input Noise Voltage and Noise Current vs Frequency



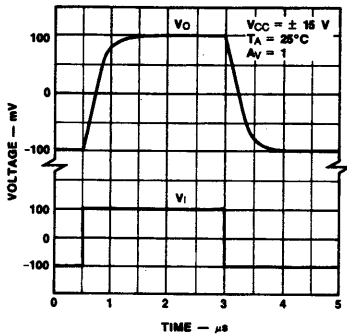
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Negative Common Mode Input Voltage Limit vs Supply Voltage



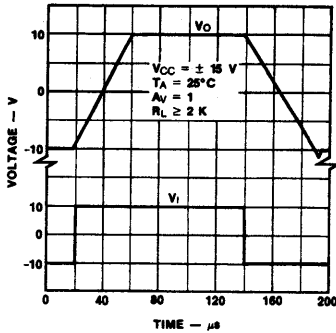
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Small Signal Pulse Response



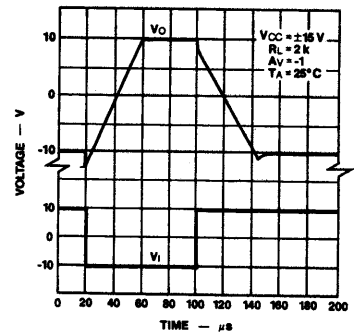
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Large Signal Pulse Response



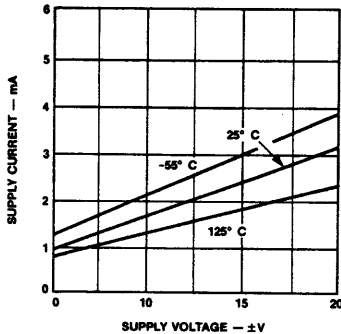
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Inverting Large Signal Pulse Response



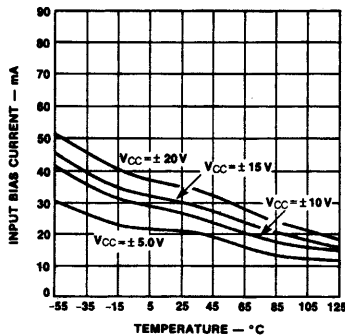
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Supply Current vs Power Supply Voltage



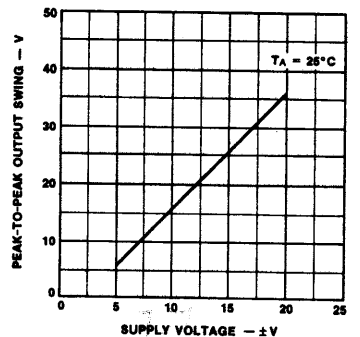
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Input Bias Current vs Ambient Temperature



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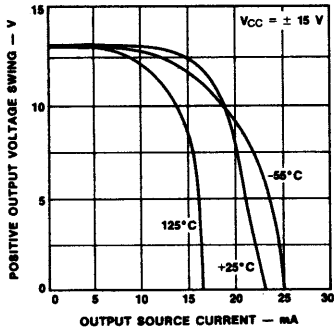
Output Voltage Swing vs Supply Voltage



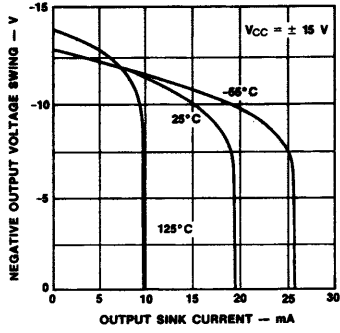
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Typical Performance Curves (Cont.)

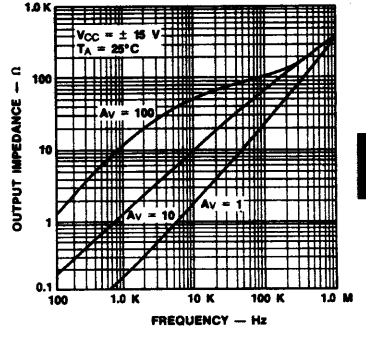
Output Voltage vs Source Current



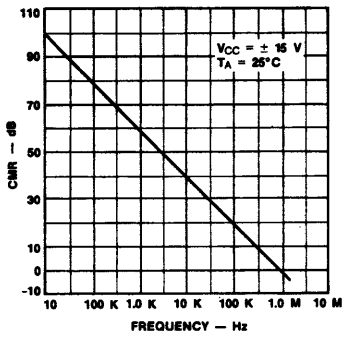
Output Voltage vs Sink Current



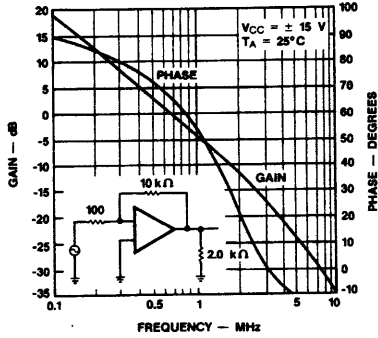
Output Impedance vs Frequency



CMR vs Frequency



Gain and Phase vs Frequency



Gain Bandwidth vs Temperature

